

TPD-1C12-007

InGaAs PIN photodiode chip

FEATURES:

- Monitor optic application.
- Low dark current and low capacitance.

ELECTRO-OPTICAL CHARACTERISTICS:

PARAMETERS	SYMBOL	MIN	TYP	MAX	UNIT	TEST CONDITIONS
Responsivity	R		0.9		A/W	$V_R=5V, \lambda=1300nm$
Breakdown Voltage	V_{BD}		18		V	$I_R=1\mu A$
Capacitance	C		1300	1500	pF	$V_R=0V, f=1\text{ MHz}$

Fig. 1 Typical Dark Current and Forward Current

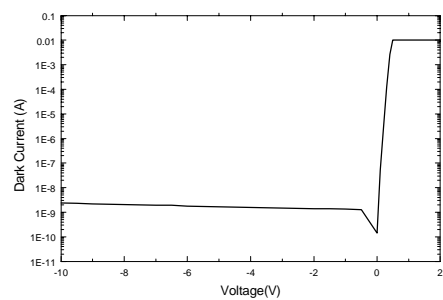


Fig. 2 Typical Photo-Current

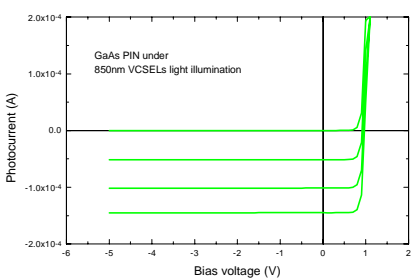


Fig. 3 Typical Breakdown Curve

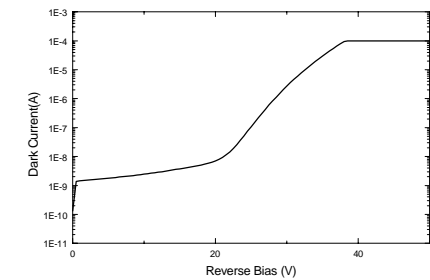
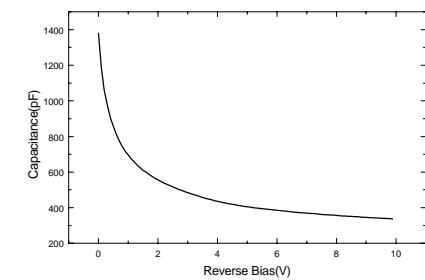
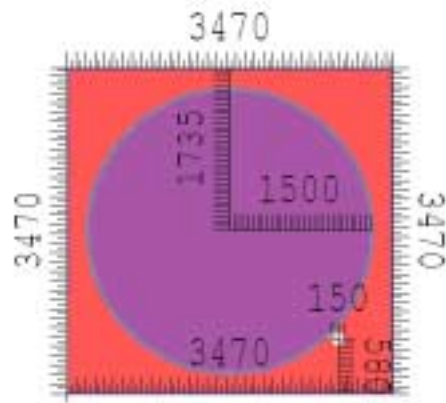


Fig. 4 Typical C-V Curve



OUTLINE DIAGRAM:



- Chip size is typical 3.47mmx3.47mm square.
- Sensitive area is typical 3mm in diameter.